

PSMN2R2-30YLC

N-channel 30 V 2.15m Ω logic level MOSFET in LFPAK using NextPower technology

Rev. 02 — 3 May 2011

Product data sheet

1. Product profile

1.1 General description

Logic level enhancement mode N-channel MOSFET in LFPAK package. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

1.2 Features and benefits

- High reliability Power SO8 package, qualified to 175°C
- Low parasitic inductance and resistance
- Optimised for 4.5V Gate drive utilising NextPower Superjunction technology
- Ultra low QG, QGD, and QOSS for high system efficiencies at low and high loads

1.3 Applications

- DC-to-DC converters
- Lithium-ion battery protection
- Load switching

- Power OR-ing
- Server power supplies
- Sync rectifier

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C		-	-	30	V
I _D	drain current	T_{mb} = 25 °C; V_{GS} = 10 V; see <u>Figure 1</u>	[1]	-	-	100	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>		-	-	141	W
Tj	junction temperature			-55	-	175	°C
Static cha	aracteristics						
R _{DSon}	drain-source on-state resistance	$V_{GS} = 4.5 \text{ V}; I_D = 25 \text{ A};$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 12}}{\text{Figure 12}}$		-	2.3	2.8	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A};$ $T_i = 25 \text{ °C}; \text{ see Figure 12}$		-	1.8	2.15	mΩ



Table 1. Quick reference data ...continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Dynamic	characteristics					
Q_{GD}	gate-drain charge	$V_{GS} = 4.5 \text{ V}; I_D = 25 \text{ A};$ $V_{DS} = 15 \text{ V}; \text{ see } \frac{\text{Figure 14}}{\text{see } \frac{\text{Figure 15}}{\text{Figure 15}}}$	-	8	-	nC
Q _{G(tot)}	total gate charge	$V_{GS} = 4.5 \text{ V}$; $I_D = 25 \text{ A}$; $V_{DS} = 15 \text{ V}$; see Figure 14; see Figure 15	-	26	-	nC

^[1] Continuous current is limited by package.

2. Pinning information

Table 2. Pinning information

		,		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source		_
2	S	source	mb	D
3	S	source		
4	G	gate		
mb	D	mounting base; connected to drain	1 2 3 4	mbb076 S
			SOT669 (LFPAK; Power-SO8)	

3. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
PSMN2R2-30YLC	LFPAK; Power-SO8	plastic single-ended surface-mounted package; 4 leads	SOT669		

4. Marking

Table 4. Marking codes

Type number	Marking code ^[1]
PSMN2R2-30YLC	2C230L

^{[1] % =} placeholder for manufacturing site code

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C		-	30	V
V_{DGR}	drain-gate voltage	25 °C \leq T _j \leq 175 °C; R _{GS} = 20 k Ω		-	30	V
V _{GS}	gate-source voltage			-20	20	V
I _D	drain current	$V_{GS} = 10 \text{ V}; T_{mb} = 25 \text{ °C}; \text{ see } \frac{\text{Figure 1}}{\text{Model}}$	[1]	-	100	Α
		$V_{GS} = 10 \text{ V}; T_{mb} = 100 \text{ °C}; \text{ see } \frac{\text{Figure 1}}{\text{Model}}$	[1]	-	100	Α
I _{DM}	peak drain current	pulsed; $t_p \le 10 \mu s$; $T_{mb} = 25 \text{ °C}$; see Figure 4		-	765	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>		-	141	W
T _{stg}	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
T _{sld(M)}	peak soldering temperature			-	260	°C
V _{ESD}	electrostatic discharge voltage	MM (JEDEC JESD22-A115)		630	-	V
Source-drain of	diode					
Is	source current	T _{mb} = 25 °C	[1]	-	100	Α
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$		-	765	Α
Avalanche rug	gedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 100 A; $V_{sup} \le$ 30 V; R_{GS} = 50 Ω; unclamped; see Figure 3		-	92	mJ

[1] Continuous current is limited by package.

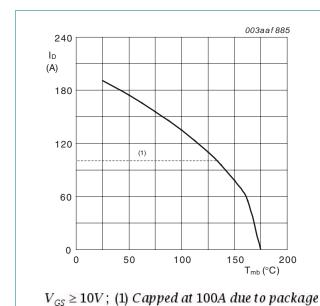


Fig 1. Continuous drain current as a function of mounting base temperature

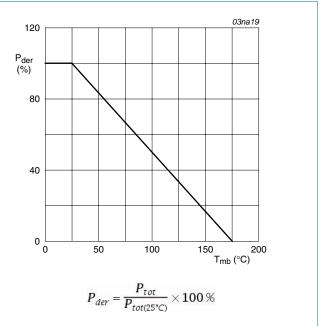


Fig 2. Normalized total power dissipation as a function of mounting base temperature

PSMN2R2-30YLC

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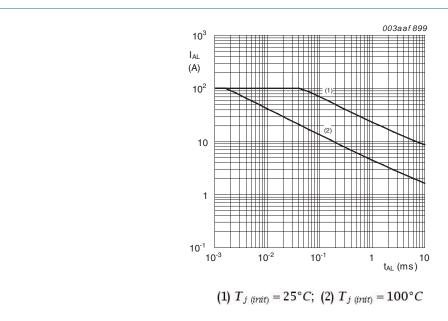
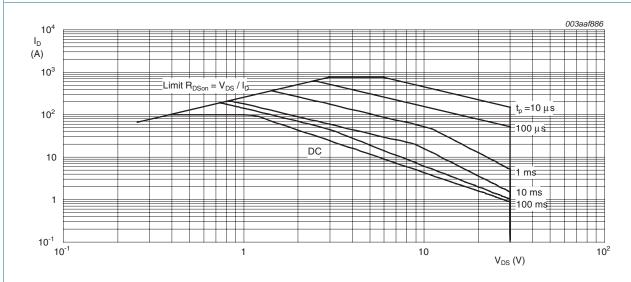


Fig 3. Single pulse avalanche rating; avalanche current as a function of avalanche time



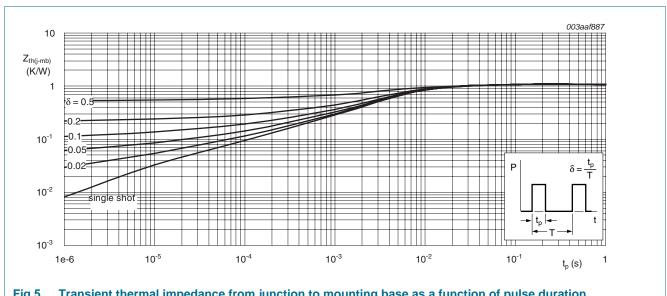
 $T_{mb} = 25$ °C; I_{DM} is a single pulse

Fig 4. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

Thermal characteristics

Table 6. **Thermal characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 5	-	0.92	1.06	K/W



Transient thermal impedance from junction to mounting base as a function of pulse duration

7. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	cteristics					
V _{(BR)DSS}	drain-source breakdown	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	30	-	-	V
	voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 °C$	27	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1$ mA; $V_{DS} = V_{GS}$; $T_j = 25$ °C; see Figure 10; see Figure 11	1.05	1.49	1.95	V
		$I_D = 10 \text{ mA}; V_{DS} = V_{GS}; T_j = 150 \text{ °C}$	0.5	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C}$	-	-	2.25	V
I _{DSS}	drain leakage current	$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	1	μΑ
		$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 150 \text{ °C}$	-	-	100	μΑ
I _{GSS}	gate leakage current	$V_{GS} = 16 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	100	nΑ
		$V_{GS} = -16 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	100	nΑ
R_{DSon}	drain-source on-state resistance	$V_{GS} = 4.5 \text{ V}; I_D = 25 \text{ A}; T_j = 25 ^{\circ}\text{C};$ see Figure 12	-	2.3	2.8	mΩ
	$V_{GS} = 4.5 \text{ V}$; $I_D = 25 \text{ A}$; $T_j = 150 \text{ °C}$; see <u>Figure 12</u> ; see <u>Figure 13</u>	-	-	4.6	mΩ	
	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ °C};$ see Figure 12	-	1.8	2.15	mΩ	
	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 150 °C;$ see Figure 12; see Figure 13	-	-	3.55	mΩ	
R_{G}	gate resistance	f = 1 MHz	-	8.0	1.6	Ω
Dynamic ch	aracteristics					
Q _{G(tot)} total gate charge	$I_D = 25 \text{ A}$; $V_{DS} = 15 \text{ V}$; $V_{GS} = 10 \text{ V}$; see <u>Figure 14</u> ; see <u>Figure 15</u>	-	55	-	nC	
		$I_D = 25 \text{ A}$; $V_{DS} = 15 \text{ V}$; $V_{GS} = 4.5 \text{ V}$; see <u>Figure 14</u> ; see <u>Figure 15</u>	-	26	-	nC
		$I_D = 0 \text{ A}; V_{DS} = 0 \text{ V}; V_{GS} = 10 \text{ V}$	-	21	-	nC
Q_{GS}	gate-source charge	$I_D = 25 \text{ A}; V_{DS} = 15 \text{ V}; V_{GS} = 4.5 \text{ V};$	-	7.3	-	nC
Q _{GS(th)}	pre-threshold gate-source charge	see <u>Figure 14</u> ; see <u>Figure 15</u>	-	5.2	-	nC
Q _{GS(th-pl)}	post-threshold gate-source charge		-	2.1	-	nC
Q_{GD}	gate-drain charge		-	8	-	nC
V _{GS(pI)}	gate-source plateau voltage	$I_D = 25 \text{ A}$; $V_{DS} = 15 \text{ V}$; see <u>Figure 14</u> ; see <u>Figure 15</u>	-	2.43	-	V
C _{iss}	input capacitance	$V_{DS} = 15 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$	-	3310	-	pF
C _{oss}	output capacitance	$T_j = 25 ^{\circ}\text{C}$; see Figure 16	-	651	-	pF
C _{rss}	reverse transfer capacitance		-	239	-	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 15 \text{ V}; R_L = 0.6 \Omega; V_{GS} = 4.5 \text{ V};$	-	26	-	ns
t _r	rise time	$R_{G(ext)} = 4.7 \Omega$	-	36	-	ns
t _{d(off)}	turn-off delay time		-	47	-	ns
t _f	fall time		-	23	-	ns

Table 7. Characteristics ... continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit	
Q _{oss}	output charge	$V_{GS} = 0 \text{ V}; V_{DS} = 15 \text{ V}; f = 1 \text{ MHz};$ $T_j = 25 \text{ °C}$	-	18.4	-	nC	
Source-drain	Source-drain diode						
V _{SD}	source-drain voltage	$I_S = 25 \text{ A}$; $V_{GS} = 0 \text{ V}$; $T_j = 25 \text{ °C}$; see Figure 17	-	0.8	1.1	V	
t _{rr}	reverse recovery time	$I_S = 25 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s};$	-	37	-	ns	
Q _r	recovered charge	$V_{GS} = 0 \text{ V}; V_{DS} = 15 \text{ V}$	-	37	-	nC	
t _a	reverse recovery rise time	$V_{GS} = 0 \text{ V}; I_S = 25 \text{ A};$	-	21	-	ns	
t _b	reverse recovery fall time	$dI_S/dt = -100 \text{ A/}\mu\text{s}; V_{DS} = 15 \text{ V};$ see Figure 18	-	16	-	ns	

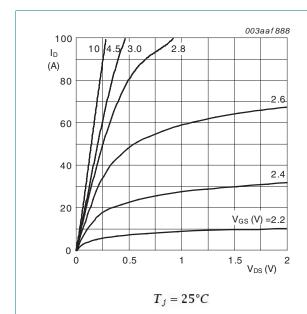


Fig 6. Output characteristics; drain current as a function of drain-source voltage; typical values

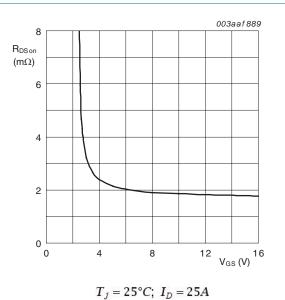


Fig 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

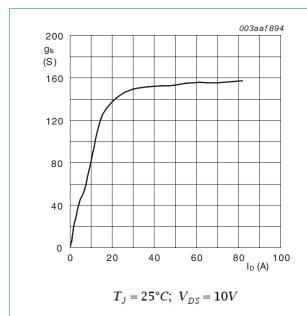


Fig 8. Forward transconductance as a function of drain current; typical values

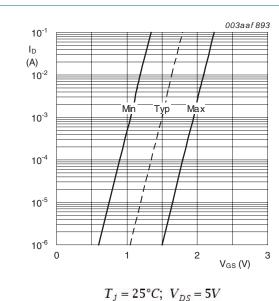


Fig 10. Sub-threshold drain current as a function of gate-source voltage

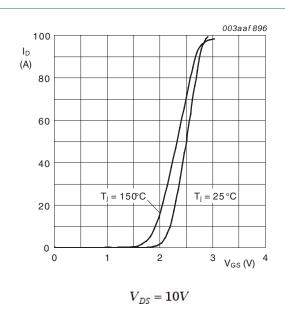


Fig 9. Transfer characteristics; drain current as a function of gate-source voltage; typical values

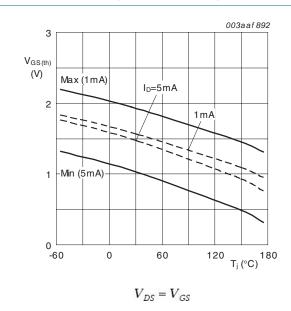


Fig 11. Gate-source threshold voltage as a function of junction temperature

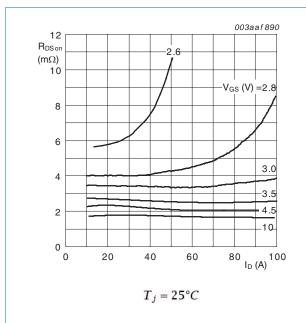


Fig 12. Drain-source on-state resistance as a function of drain current; typical values

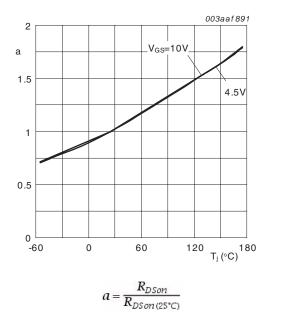


Fig 13. Normalized drain-source on-state resistance factor as a function of junction temperature

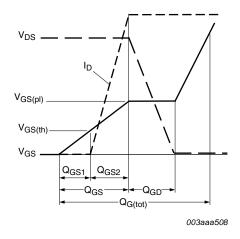
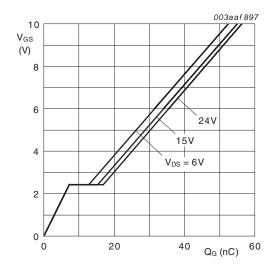


Fig 14. Gate charge waveform definitions



 $T_j = 25^{\circ}C; \ I_D = 25A$

Fig 15. Gate-source voltage as a function of gate charge; typical values

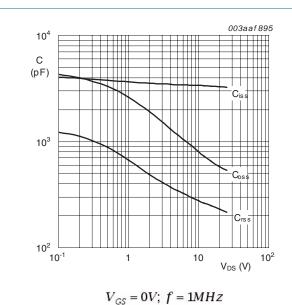


Fig 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

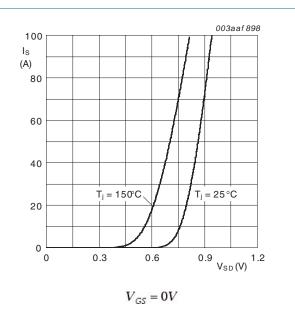


Fig 17. Source current as a function of source-drain voltage; typical values

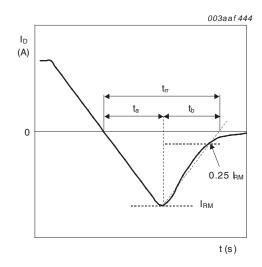


Fig 18. Reverse recovery timing definition

Package outline

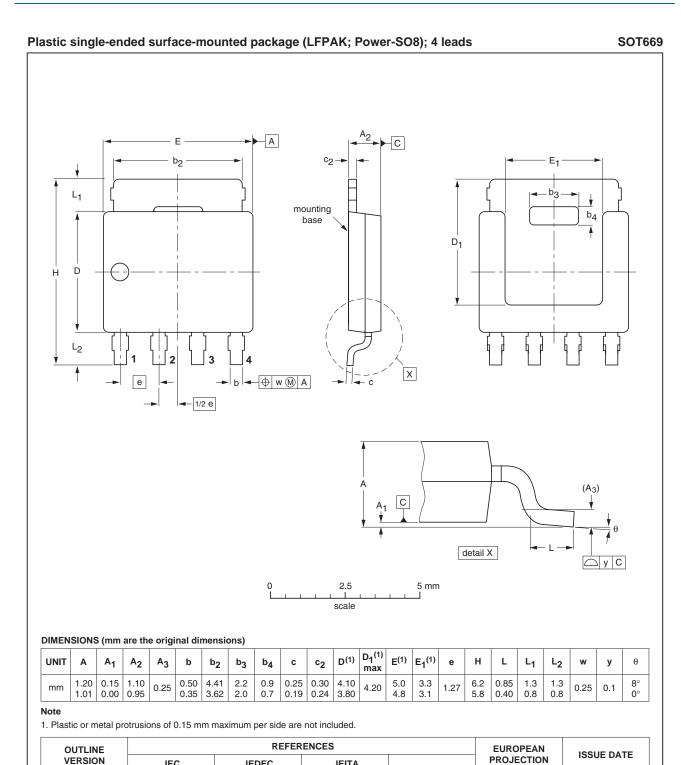


Fig 19. Package outline SOT669 (LFPAK; Power-SO8)

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SOT669

9. Revision history

Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes		
PSMN2R2-30YLC v.2	20110503	Product data sheet	-	PSMN2R2-30YLC v.1		
Modifications:	Status changed from preliminary to product.					
	 Various changes to 	o content.				
PSMN2R2-30YLC v.1	20110317	Preliminary data sheet	-	-		

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10.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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PSMN2R2-30YLC

N-channel 30 V $2.15m\Omega$ logic level MOSFET in LFPAK using NextPower

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